Optoelectronic Properties and Defect Engineering of Highly Efficient Lead-free Photovoltaic Absorbers Cs$_2$Au$^\text{I}^\text{II}$X$_6$ (X=I, Br)

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Stability and toxicity issues of hybrid lead iodide perovskite MAPbI$_3$ necessitate potential alternatives. Here we shed new light on promising photovoltaic properties of Gold mixed valence halide perovskites, satisfying fundamental requirements i.e. non-toxicity, stability, band gap in visible range, low excitonic binding energy etc.. Our study shows, favourable electronic structure resulting in high optical transition strength, thus sharp rise in absorption spectra near band gap yielding very high short circuit current density and hence gives higher simulated efficiency than MAPbI$_3$, for Cs$_2$Au$_2$I$_6$ and Cs$_2$Au$_2$Br$_6$. Careful investigation of defect physics reveals possibility of deep level halide vacancies in Cs$_2$Au$_2$I$_6$, but fairly less for Cs$_2$Au$_2$Br$_6$. Keeping Iodine moderate to rich and moderate cation in the growth environment for Cs$_2$Au$_2$I$_6$, while keeping anion moderate to poor and cation moderate to rich for Cs$_2$Au$_2$Br$_6$, may help achieve best possible efficiencies from both. We propose Cs$_2$Au$_2$X$_6$; (X=I, Br) to be the next generation potential solar absorber, with proper precautions taken during synthesis.

I. INTRODUCTION

Since its inception in 2009, hybrid lead halide perovskite has become the center of attention in the photovoltaic community. High optical absorption and defect tolerance made its efficiency as high as 22.1%, almost comparable to commercial silicon solar cells.[1–3] Despite being highly efficient, it still has not been commercialized till date, mainly due to two reason, (i) poor stability in ambient environment (ii) toxicity due to Pb. While replacing the organic cation with inorganic Cs has helped in stability, but the presence of Pb seems insurmountable till now. A lot has been proposed as alternatives but either they were even more unstable or the efficiency is low.[4–7] One of the key alternatives which emerges recently are double perovskite halides, A$_2$BBX$_6$[8] where A is Cs, X is one of the halides, and B, B$'$ are +1, +3 elements or vice versa. There exists various theoretical and experimental studies exploring different B, B$'$ combinations, but most of these compounds either have indirect band gap (leading to higher recombination loss) or the gap is in high violet region due to the optically forbidden transition (leading to poor absorption).[9–11] Some solution has been reported showing indirect to direct transition but toxicity was still a concern.[12–14]

Cs$_2$Au$_2$X$_6$ (X=I, Br, Cl) are a class of compounds which show semiconducting behavior at ambient condition.[15, 16] Although the predicted band gaps for these materials are quite favorable for solar absorption, however they were never being investigated from the photovoltaic perspective. Very recently, Debshichi et al.[17] reported a theoretical study on Cs$_2$Au$_2$I$_6$ and proposed it as a promising photovoltaic absorber. This was further confirmed by Giorgi et al.[18] who showed the presence of weakly bound excitons in this compound, (similar to MAPbI$_3$) hinting towards good photovoltaic performance. However, few key points are not properly addressed in these studies e.g. (i) correct nature of band gap (ii) estimate of solar efficiency. In addition, these studies are only focused on Cs$_2$Au$_2$I$_6$ compound, although the other halide compounds also have band gap in the visible range. Apart from these, defect physics of these compounds has never been studied. This is extremely important because defects in photovoltaic materials play a crucial role in dictating the device efficiency. For example, presence of a deep level defect which can act as electron-hole recombination center, limits the carrier diffusion to a greater extent.[19] While synthesizing, it is therefore very important to create a chemical environment which minimizes the defect concentration in a compound.

In this paper, we have performed a careful first principle calculation to study the electronic, structural, and optical properties of the full series Cs$_2$Au$_2$X$_6$ (X=I, Br, Cl) from a perspective of photovoltaic applications. Careful analysis of band structure reveals slightly indirect nature of band gap, in complete contrast to earlier reports.[17, 18] This indeed impacts the photovoltaic properties of these compounds. Chemical, mechanical, and dynamical stability of all the compounds are also studied. In addition, we have investigated the possibility of point defect formation under various growth environment and found that even in iodine rich condition, iodine vacancies are highly probable to form in Cs$_2$Au$_2$I$_6$. On the other hand, probability of defect formation in Cs$_2$Au$_2$Br$_6$ is less, which also has a band gap in near visible range, and hence a better candidate as photovoltaic absorber, compared to Cs$_2$Au$_2$I$_6$. Additionally, we have also simulated the series of compounds made of

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organic cations MA(CH$_3$NH$_3^+$), FA(CH(NH$_2$)$_2^+$) in place of Cs and investigated their possibility of formation and potential for photovoltaic applications. All the calculations are done by employing first principles Density Functional Theory (DFT)\cite{20} using Vienna Ab-initio Simulation Package (VASP).\cite{21, 22} Other details of the calculations are given in the Appendix A.

II. STRUCTURAL DETAILS AND STABILITY

Under the ambient condition, Cs$_2$Au$_2$X$_6$ (X=I, Br, Cl) crystallizes in distorted double perovskite structure with space group I4/mmm (139). In this structure, Cs atoms sit at 4d Wyckoff site, Au(1) and Au(2) at 2h and 2a respectively while the anion sits at two inequivalent 4e and 8h sites. Here Au(1) and Au(2) possess +1, and +3 oxidation state respectively, making it possible to have all the features of double perovskite. Halogens form alternate linear [Au(1)X$_2$]$^-$, and square-planar [Au(2)X$_4$]$^-$ complexes.\cite{15, 16} The presence of alternately arranged elongated, and compressed AuI$_6$ octahedra can be seen in Figure.1(a), and can be confirmed from respective Au-X bond lengths (see SM\cite{23}), which matches well with previous experimentally reported data.\cite{24}

First, we checked the chemical, mechanical, and dynamical stability of these compounds. For chemical stability, we have calculated the formation enthalpy ($\Delta H_f$) against the binary halides in the following pathway: M$_2$Au$_2$X$_6$ $\rightarrow$ 2MX + AuX + AuX$_3$ (M=Cs, MA, FA; X=I, Br, Cl). They are presented in Table I. Going from I $\rightarrow$ Br $\rightarrow$ Cl, the chemical stability increases. For mechanical stability, we calculated the elastic constants (tabulated in SM\cite{23}) which satisfies the Born Huang mechanical stability criteria for all three halides.\cite{25} Calculated phonon dispersions (shown in SM\cite{23}) show no imaginary frequencies, and hence confirms the dynamical stability.

III. ELECTRONIC STRUCTURE

Figure. 1(c, d, e) shows the HSE06 electronic band structure of the three compounds. Cs$_2$Au$_2$I$_6$ forms an intermediate band comprised mainly of Au(2) 5d$_{z^2}$ and I-p orbitals, which is responsible for its band gap (1.31 eV) in the visible range.\cite{18, 26} The valence band maxima (VBM) consists mainly of Au(1) 5d$_{z^2}$ and I-p orbital. In case of Br and Cl, orbital contributions seem to be similar, but the band gap increases due to increase in nearest neighbor Coulomb interaction and Jahn-Teller distortion.\cite{15} For better accuracy, we have used HSE06 functional to simulate the band edge information,\cite{27} whereas, the band gap values are calculated from an even more accurate HSE06-GW functional. Our calculation reveals that all these materials have a slightly indirect band gap, having VBM and CBM at different points along $\Gamma$ to $\Sigma'$ direction. This is in complete contrast to the previous studies\cite{17, 18}, where a direct band gap is predicted at high symmetry N-point. This was because these studies have not taken the important $\Gamma'$-$\Sigma'$ direction in their band structure calculation, where the actual VBM and CBM lies. We have also calculated the dipole transition matrix elements (aka transition probability) showing allowed optical transition at direct band gap [see Figure. S2 of SM\cite{23}]. High transition strength
indicating the possibility of high absorption can be attributed to the mixing of halogen p and Au d orbitals.\cite{28} Table I shows our simulated band gap along with the difference between indirect and optically allowed direct gap ($\Delta E_g^\text{dir}$). Our simulated band gaps matches fairly well with previously reported experimental values.\cite{15} We have also checked the properties of organic cation namely MA and FA counterpart of these compounds. Our calculated lattice parameters for MA$_2$Au$_2$I$_6$ agrees well with previous experimental data.\cite{29} All the other electronic structure data along with the band structure and transition probabilities are shown in SM.\cite{23} All the organic mixed valence gold perovskite compounds show fairly large band gap, restricting their application as photovoltaic absorber.

\section*{IV. Absorption Coefficient and Spectroscopic Limited Maximum Efficiency (SLME)}

Finite values of calculated transition probability encourage us to simulate the next relevant parameters for photovoltaic applications, i.e. absorption coefficients and spectroscopic limited maximum efficiency (SLME). Details about SLME formulation is given in SM\cite{23} which is a better efficiency indicator than the bare Shockley Queisser limit.

Figure 2(a) and 2(b) show the absorption coefficients ($\alpha$) and SLME respectively for the three systems. For comparison, corresponding simulated data for MAPbI$_3$ are also shown. From Figure. 2(a), one can see that the absorption coefficient in xy-plane is order of magnitude higher than those in the z-direction, confirming strong optical anisotropy of the material.\cite{17, 18} This gives us an idea about appropriate alignment of the crystal axes so as to maximize the photo absorption. Careful analysis reveals that the first optical peak along xy-direction can be attributed to vertical transition between two highest valence states (comprising of mainly Au(1) 5d$_{z^2}$ orbitals) and two lowest conduction states (Au(2) 5d$_{z^2}$-$p^2$ and I $p_z$ orbitals), whereas along z-direction it is due to the transition from lower part of the valence band (Au(1) 5d$_{z^2}$-$p_z$) to the intermediate band, explaining the significantly higher optical absorption in xy-plane.\cite{18}

Looking at the absorption spectra one can see a sharp rise in absorption coefficient ($\alpha$) near the band gap for all three halides. Although in lower wavelength region the absorption coefficient is higher for MAPbI$_3$, but a lower band gap (for Cs$_2$Au$_2$I$_6$), and sharper rise of absorption spectra near band edge for both iodide and bromide compounds indicate better utilization of the solar spectrum. This can further be confirmed by our simulated short-circuit current density ($J_{sc}$). For completeness, we have tabulated room temperature (298 K) simulated values of few important device parameters, such as $J_{sc}$, open-circuit voltage ($V_{oc}$), current density ($J_{max}$) and voltage ($V_{max}$) at maximum power output, SLME and fill factor (FF) at film thickness 500 nm for all three halides in Table I, and compared the same with MAPbI$_3$. Notice that, $J_{sc}$ and $J_{max}$ are almost twice for Cs$_2$Au$_2$I$_6$ as compared to MAPbI$_3$, which becomes almost 1.5 times at saturation thickness. Slightly lower attainable voltage makes the efficiency 1.5 times at lower film thicknesses, and at least 3% higher at saturation thickness. A little higher band gap makes Cs$_2$Au$_2$Br$_6$ to have higher attainable voltage making the SLME much higher than MAPbI$_3$ at lower film thicknesses, while it becomes comparable when thickness goes near saturation (see Fig. 2). For Cl, efficiency remains much lower compared to the other two halides, mainly due to higher band gap resulting in much lower attainable current.
TABLE I. Formation enthalpy ($\Delta H_f$) simulated and experimental band gap ($E_g$), difference between electronic and optically allowed direct gap ($\Delta E_d^{oa}$), short circuit current density ($J_{sc}$), open circuit voltage ($V_{oc}$), current density ($J_{max}$) and voltage ($V_{max}$) at maximum power, SLME and fill factor (FF) at 298 K for the three compounds. Various device related parameters are calculated at a film thickness of 500 nm. For comparison, relevant data for MAPbI$_3$ are also tabulated. "[15] ",[30] "[3] 

V. DEFECT PHYSICS

Defects play a major role in dictating the carrier mobility, lifetime, and recombination rate for a given semiconductor. Unlike extended defects (e.g. grain boundaries, surface passivation, etc.), intrinsic point defects (vacancies, interstitials, antisites, etc.) are very difficult to control.[19, 31, 32] For example, in case of MAPbI$_3$, shallow dominant point defects[33] result in high carrier diffusion length aiding to its high efficiency. Whereas presence of deep level defects, acting as Shockley-Read-Hall (SRH) recombination centers, are known to be one of the main reasons behind significantly lower efficiency in case of kesterite (CZTS) solar cells.[31] In order to gain better insight, we performed a detailed ab-initio study of all the possible point defects in Cs$_2$Au$_2$I$_6$ and Cs$_2$Au$_2$Br$_6$, which are predicted to have comparable or higher theoretical efficiency than MAPbI$_3$.

Formation energy for a defect $D$ at a charge state $q$ is defined as,

$$E_{\text{form}}^D = E_{\text{tot}}^D - E_{\text{tot}}^{\text{bulk}} - \sum_i n_i \mu_i + q(E_{VBM} + \Delta E_F) + E_c$$

where $E_{\text{tot}}^D$ is the total energy for a supercell with the associated defect $D$ at a charge state $q$. $E_{\text{tot}}^{\text{bulk}}$ is the total energy for pure bulk supercell of equivalent size. $\mu_i$ is the chemical potential of the associated defect with $n_i$ being the number of defects added ($n_i > 0$) or removed ($n_i < 0$). The next term accounts for the chemical potential for electrons added ($q < 0$) or removed ($q > 0$) to create various charged defect states. $E_{VBM}$ is the correction term which includes the correction for breaking periodicity, and the related band alignment error.

Three types of defects are considered, vacancies (V$_{Cs}$, V$_{Au}$, V$_X$), interstitials (Cs$_i$, Au$_i$, X$_i$), and anti-sites (Cs$_{Au}$, Cs$_X$, Au$_{Cs}$, Au$_X$, X$_{Cs}$, X$_{Au}$). (X=I, Br, etc). Two inequivalent Wyckoff positions for both X and Au are considered. To accurately calculate various defect charge state energies, a 160 atom supercell is used. It is important to realize that, $E_{\text{form}}^{D^q}$ can vary depending on the particular choice of $\mu$. A brief discussion on the relevant choice of defects and $\mu$ is detailed in Appendix B and C respectively.

We have plotted defect formation energies at two chemical growth conditions (a) anion rich, cation poor and (b) anion poor, cation rich, for Cs$_2$Au$_2$I$_6$ and Cs$_2$Au$_2$Br$_6$ in Figure 3 and 4 respectively. We have also considered a few other possible growth environments which are shown in SM.[23] Notice that the defects at inequivalent sites behave differently. It is evident that, for Cs$_2$Au$_2$I$_6$, at anion poor environment the dominant defects are V$_I$, Au$_I$, Au$_I$ antisites. V$_I$ at both iodine sites has similar formation energies and acts as deep level donors. This can be attributed to the fact that conduction band minima having anti-bonding nature, mainly comprises of Au(2)-d and I(2)-p orbitals. Also the other probable defects (Au$_I$, Au$_{I(I)}$, Cs$_{I(I)}$) are also deep level donors, which suggests that at anion poor conditions, this compound will have high n-type carrier concentration and will suffer from deep level defects (mainly V$_I$) which may act

FIG. 4. Same as figure 3, but for Cs$_2$Au$_2$Br$_6$.
as SRH recombination center, and hence hinder its photovoltaic performance. Noticeably, even at anion rich condition, probability of $V_I$ mainly at I(1) is still high, which might be compensated by formation of $V_{Cs}$ (main acceptor), pinning the Fermi level at middle of the band gap. At this condition, $I_{Cs}$ and $I_{Au}$ antisites will be dominant defect but they seemed to maintain their neutral charge state. So, we can conclude that at anion rich condition, although there might be an overall p-type, n-type cancellation, the presence of deep level defects can still cause high non-radiative recombination thus causing small carrier diffusion length. From Figure 4, one can see that the formation energy of Br vacancy is higher compared to Iodine. In fact, concentration of all the possible deep level defects can be greatly reduced by maintaining an anion moderate environment, in case of Br, thus making it better in terms of defect tolerance. From the supplement,[23] it can be seen that keeping I moderate to rich, and moderate cation in the growth environment can be the best possible scenario to synthesize $Cs_2Au_2I_6$. While for $Cs_2Au_2Br_6$, keeping Br moderate to poor, and cations moderate to rich can be ideal. Overall, lower possibility of deep level defect formation in $Cs_2Au_2Br_6$ not only makes it a practically better candidate to achieve higher efficiency than its iodine counterpart but also makes its synthesis more flexible.

VI. CONCLUSION

In summary, we predicted $Cs_2Au_2X_6$ ($X$=I, Br) to be highly efficient potential active material for photovoltaic solar cells, with several favorable properties such as non-toxicity, better stability and efficiency etc. A careful first principles calculations predicted these compounds to have slightly indirect nature of band gap, contrary to previously reported data. Optically allowed direct band gap, however, remains very close (within 20 meV) to the indirect gap, allowing the optical absorption to be very high. Band gap nearly in the ideal visible region and sharp rise of absorption coefficient near band edge gives the simulated efficiency even higher than state of the art MAPbI$_3$, even at very small film thickness. Our detailed study on defect physics predicted vacancies $V_X$ and $V_{Cs}$ to be the most important donor and acceptor type defects respectively. In the case of $Cs_2Au_2I_6$, the chances of deep level defect formation are very high making it prone to carrier loss due to non-radiative recombination. While for Br, possibility of these defect formation is much lesser thus making it a more suitable candidate. We also propose suitable growth environment for both $Cs_2Au_2I_6$ and $Cs_2Au_2Br_6$ under which defects can be minimized and best possible efficiency can be achieved. We propose $Cs_2Au_2X_6$ to be the next generation promising photovoltaic material after MAPbI$_3$ and anticipate immediate attention of experimentalists to prepare and test thin film photovoltaic cells based on $Cs_2Au_2X_6$ ($X$=I, Br).[34–38]

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APPENDIX A: COMPUTATIONAL DETAILS

All the calculations are done using Density Functional Theory (DFT) [20] as implemented in Vienna Ab-initio Simulation Package (VASP) [21, 22] with projector augmented Wave (PAW) basis set. Finding the equilibrium structure, calculation of decomposition enthalpy and other primary electronic structure (band structure, density of states etc.) were done using Perdew-Burke-Ernzerhof (PBE) exchange correlation functional.[39] Cs (5s$^2$5p$^6$6s$^1$), Au (5d$^{10}$6s$^1$), I (5s$^2$5p$^5$), Br (4s$^2$4p$^5$), Cl (3s$^2$3p$^5$), C (2s$^2$2p$^2$), N (2s$^2$2p$^3$), and H (1s$^1$) are used as valence electrons. An energy cutoff 500 eV with 6×6×6 Γ centered k-mesh is considered for structural optimization and are relaxed until forces reached to the value less than 0.001 eV/Å for $Cs_2Au_2X_6$: $X$=I, Br, Cl. For organic gold halides, we have replaced the Cs with MA (CH$_3$NH$_3$) and FA (CH(NH$_2$)$_2$) cations in the relaxed $Cs_2Au_2I_6$ structure and then relaxed in 3 steps. At first, we did full geometrical relaxation then again performed relaxation with parameters keeping volume and shape fixed and at last we did full geometrical relaxation with 500 eV with 6×6×6 kpoints until forces converge to 0.01 eV/Å. Charge densities were calculated using energy cutoff of 450 eV, 8×8×8 k-mesh using the relaxed structures until energy converges up to 10$^{-6}$ eV. Next, we have used Heyd-Scuseria-Ernzerhof (HSE06)[27] functional to get the band edge information. To obtain more accurate value of band gap we have used G0W0 method along with HSE06 and PBE exchange correlation functional. Optical absorption coefficients are calculated within the independent particle approximation with PBE exchange correlation functional and then scissor shifted to experimental band gap while calculating the SLME. For simulation of various defects at different charge states, we have used 520 eV plane wave energy cutoff along with gamma centered k-mesh. For each defect in different charge states, we have only relaxed the ionic positions keeping the cell shape and volume fixed.
APPENDIX B: CHOICE OF DEFECTS

Three types of defects are considered, vacancies ($V_{Cs}$, $V_{Au}$, $V_X$), interstitials ($Cs_i$, $Au_i$, $X_i$), and anti-sites ($Cs_{Au}$, $Cs_X$, $Au_{Cs}$, $Au_X$, $X_{Cs}$, $X_{Au}$), ($X$=I,Br), etc.. For these compounds, there are two inequivalent Wyckoff positions for both halides, X and Au, which we have considered while considering the vacancy and anti-site defects. For the interstitials, we have considered all the possible positions and chose the final position based on the total energy calculation at neutral charge state. Here we have used PYCDT code[40] to generate the defects. To accurately calculate the various defect charge state energies a 160 atom supercell is used.

APPENDIX C: CHOICE OF CHEMICAL POTENTIALS FOR DEFECT FORMATION ENERGY CALCULATION

Formation energy for a defect $D$ at a charge state ‘q’ is defined as,

$$E_{\text{form}}[D^q] = E_{\text{tot}}[D^q] - E_{\text{tot}}[\text{bulk}] - \sum_i n_i \mu_i + q(E_{VB} + \Delta E_F) + E_c$$

In the above equation, we can see that defect formation energies can be varied depending on the choice of $\mu$. Experimentally, this chemical potential can vary depending on the growth environment. The choice of $\mu$ generally depends on the stability of the compound against possible elemental and competing secondary phases. As secondary phases, we have considered the most stable binary halides and other super-ordered structures of the cations.

First for the compound to be stable the below thermodynamic equilibrium must be reached,

$$2\Delta \mu_{Cs} + 2\Delta \mu_{Au} + 6\Delta \mu_{X} = \Delta H_f (X = Br, I) \quad (1)$$

Here, $\Delta H_f$ is the formation enthalpy of the compound against its elemental constituents. $\Delta \mu_i = \mu_i - \mu_i^0$ where $\mu_i^0$ is total energy of constituent $i$ at its elemental phase. Following are a set of equations, which should be satisfied to avoid coexistence of elemental and secondary phases,

$$\Delta \mu_i < 0, \ i = Cs, Au, X \quad (2)$$

$$a\Delta \mu_{Cs} + b\Delta \mu_{Au} + c\Delta \mu_{X} < \Delta H_f (Cs_{Au}X_{6}) \quad (3)$$

Here, $a,b,c=0,1,2,...Z$. Elemental chemical potential data at different points of the phase diagram (indicating different growth conditions) are taken from Materials Project database.[41] Here we show the defect formation energies for $Cs_2Au_2X_6$: $X$=I, Br, at different growth conditions. The elemental chemical potential data are taken from Materials project database.[41]
IIIB. brief discussion about SLME can be found which includes ref [35–38].


